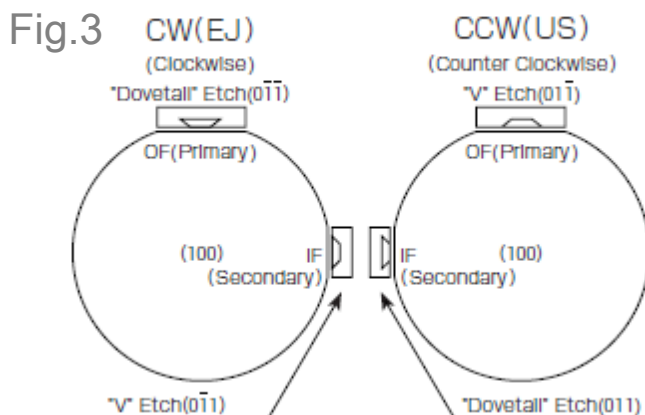
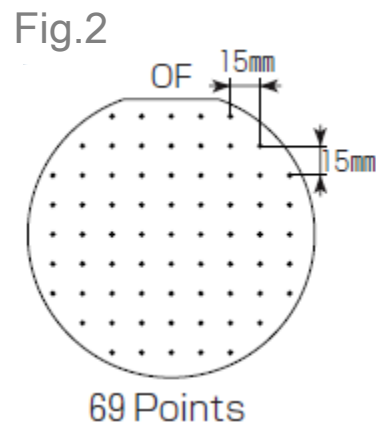
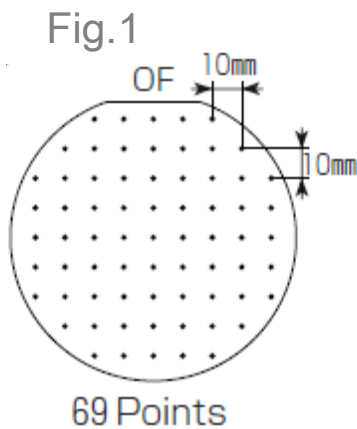


# GaAs Single Crystal Wafers for LEDs

## Standard Specifications(VB)

Conduction Type	n-Type	
Growth Method · Dopant	VB · Si	
Carrier Concentration( $\text{cm}^{-3}$ )	$2 \sim 35 \times 10^{17}$	
Resistivity( $\Omega \cdot \text{cm}$ )	$1 \sim 15 \times 10^{-3}$	
Mobility( $\text{cm}^2/\text{V} \cdot \text{sec}$ )	$1.4 \sim 3.5 \times 10^3$	
EPD Average( $\text{cm}^{-2}$ )	$\leq 5 \times 10^3$	
Measuring Points of EPD	Fig.1	Fig.2
Diameter(mm)	$100.0 \pm 0.3$	$150.0 \pm 0.3$
OF(mm)(Fig. 3)	$32.5 \pm 1.0$	$48.0 \pm 1.0$
IF(mm)(Fig. 3)	$18.0 \pm 1.0$	$30.0 \pm 1.0$
Edge Rounding(mmR)	0.25(Conform to SEMI Standards)	
Thickness( $\mu\text{m}$ )	$350 \pm 25$	$675 \pm 25$
Orientation	$(100) \pm 0.3^\circ$ , $(100)2^\circ \sim 15^\circ \text{ off} \pm 0.3^\circ$	
Surface Finish	P/E, P/P	
Surface Clean	SC-E(Super Clean Type E)	
Package	Cassette / Individual Container	



## Attached Data

· Standard : Carrier Concentration, Resistivity, Mobility, EPD Average, Diameter, OF, IF, Thickness(min. ~ max.)